

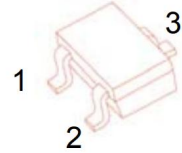
# Plastic-Encapsulate MOSFETS

N-channel MOSFET

## FEATURES

- Low on-resistance
- Fast switching speed
- Low voltage drive makes this device ideal for portable equipment
- Easily designed drive circuits
- Easy to parallel

Marking: KN

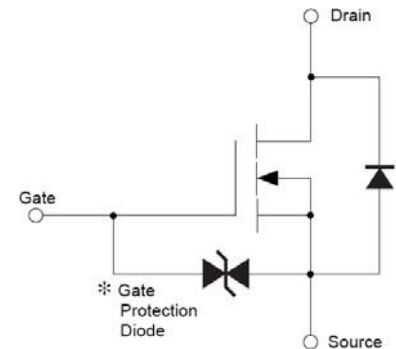


1. Gate 2. Source 3. Drain  
SOT-323 Plastic Package

## MOSFET MAXIMUM RATINGS (Ta = 25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V <sub>DS</sub>	Drain-Source Voltage	30	V
V <sub>GSS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub>	Continuous Drain Current	0.1	A
R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient	833	°C /W
P <sub>D</sub>	Power Dissipation	0.2	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55~+150	°C

## Equivalent circuit



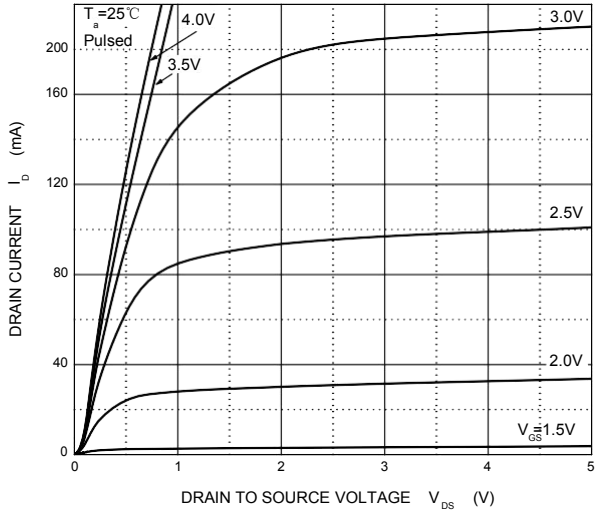
## MOSFET ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 10μA	30			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V			1	μA
Gate –Source leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V			±2	μA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = 3V, I <sub>D</sub> = 100μA	0.8		1.5	V
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 4V, I <sub>D</sub> = 10mA			8	Ω
		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 1mA			13	Ω
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = 3V, I <sub>D</sub> = 10mA	20			mS
<b>Dynamic Characteristics*</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 5V, V <sub>GS</sub> = 0V, f = 1MHz		13		pF
Output Capacitance	C <sub>oss</sub>			9		pF
Reverse Transfer Capacitance	C <sub>rss</sub>			4		pF
<b>Switching Characteristics*</b>						
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>GS</sub> = 5V, V <sub>DD</sub> = 5V, I <sub>D</sub> = 10mA, R <sub>g</sub> = 10Ω, R <sub>L</sub> = 500Ω,		15		ns
Rise Time	t <sub>r</sub>			35		ns
Turn-Off Delay Time	t <sub>d(off)</sub>			80		ns
Fall Time	t <sub>f</sub>			80		ns

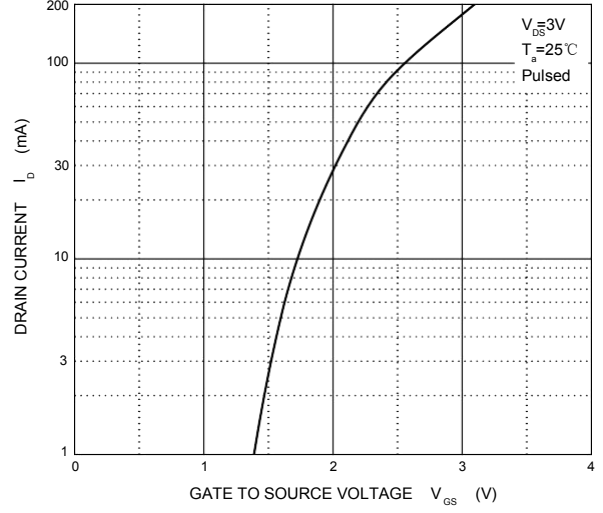
\* These parameters have no way to verify.

# Typical Characteristics

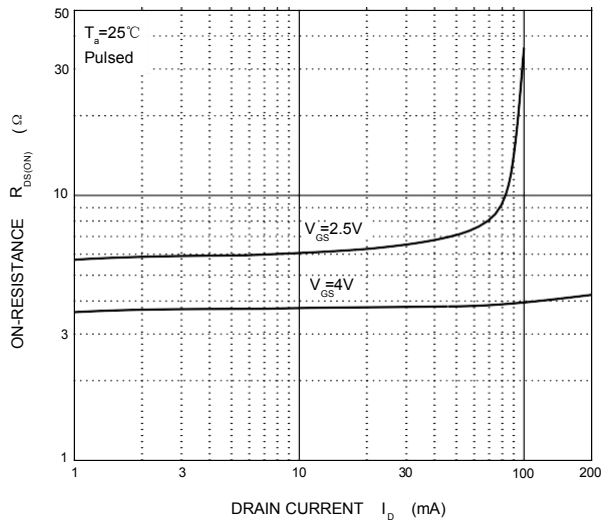
Output Characteristics



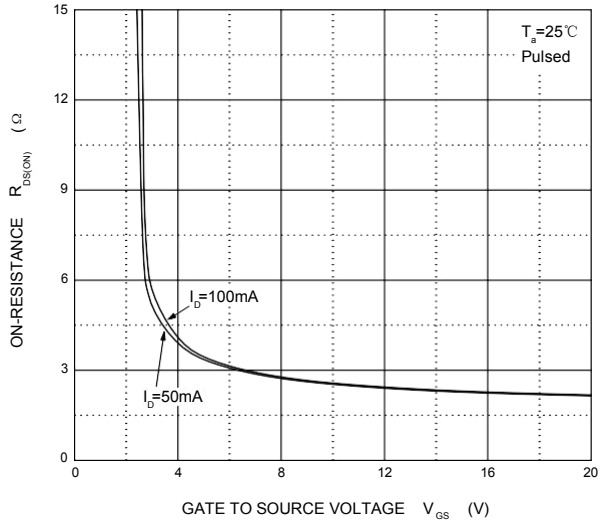
Transfer Characteristics



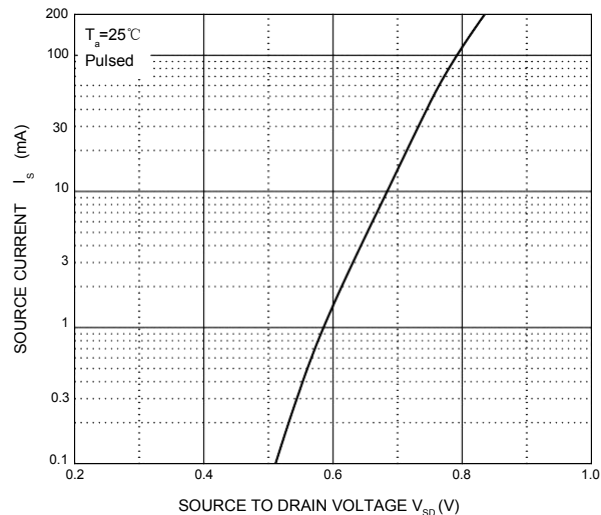
$R_{DS(ON)}$  —  $I_D$



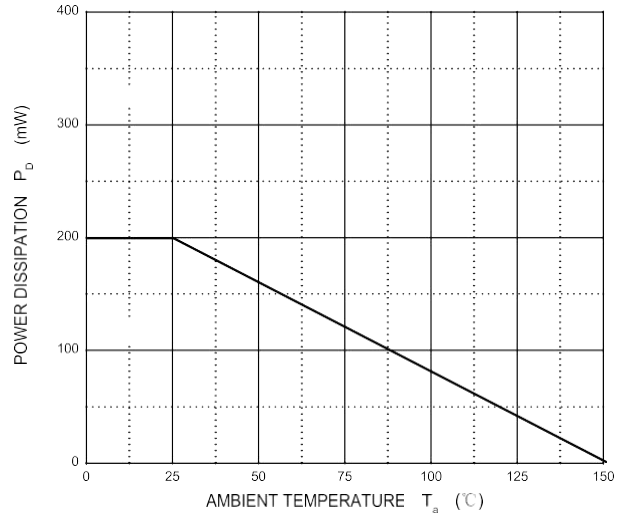
$R_{DS(ON)}$  —  $V_{GS}$



$I_S$  —  $V_{SD}$



$P_D$  —  $T_a$



## **PACKAGE OUTLINE**

**Plastic surface mounted package; 3 leads**

**SOT-323**

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